

BSS138AKA

60 V, single N-channel Trench MOSFET

29 April 2015

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	200	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C		-	2.7	4.5	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, single N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BSS138AKA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
BSS138AKA	%JL

[1] % = placeholder for manufacturing site code

60 V, single N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	200	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	125	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	800	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	300	mW
			[1]	-	360	mW
		T _{sp} = 25 °C		-	1060	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	n diode		•	•		
Is	source current	T _{amb} = 25 °C	[1]	-	200	mA

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

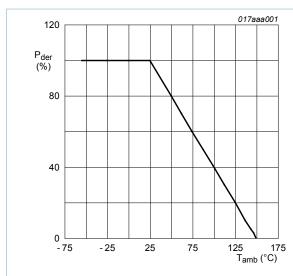


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25\%)}} \times 100\%$$

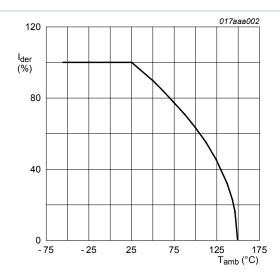


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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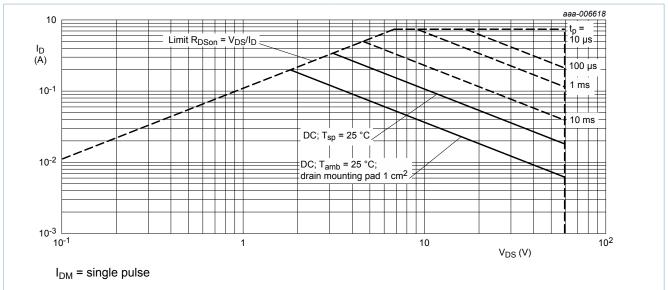


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from	thermal resistance in free air	in free air	[1]	-	350	400	K/W
	from junction to ambient		[2]	-	300	340	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

60 V, single N-channel Trench MOSFET

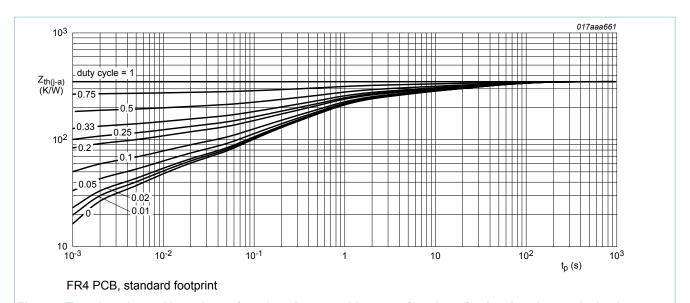


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

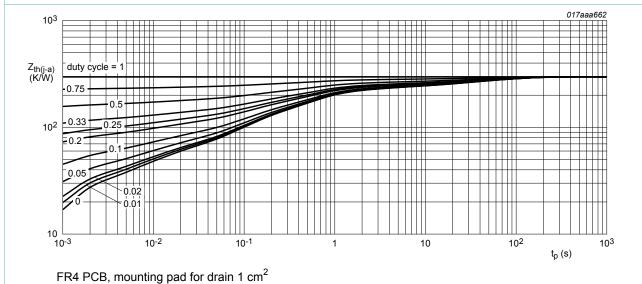


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, single N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \text{ A}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.8	1.2	1.5	V
I _{DSS} drain leak	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	3.5	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-3.5	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
	V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μΑ	
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-0.5	μΑ
200	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 100 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{j} = 25 °C	-	2.7	4.5	Ω
		V_{GS} = 10 V; I_{D} = 100 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{j} = 150 °C	-	5.5	9.2	Ω
		V_{GS} = 4.5 V; I_{D} = 100 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{j} = 25 °C	-	3	5.2	Ω
		V_{GS} = 2.5 V; I_{D} = 10 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{j} = 25 °C	-	4	13	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 150 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C	320	-	-	mS
Dynamic cl	naracteristics		'			
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 150 mA; V _{GS} = 4.5 V;	-	0.39	0.51	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	13	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.6	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; R_{L} = 250 Ω ; V_{GS} = 10 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	6	-	ns
$t_{d(off)}$	turn-off delay time		-	36	72	ns

BSS138AKA

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60 V, single N-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _f	fall time			-	22	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I_S = 115 mA; V_{GS} = 0 V; T_j = 25 °C		0.47	0.7	1.2	V

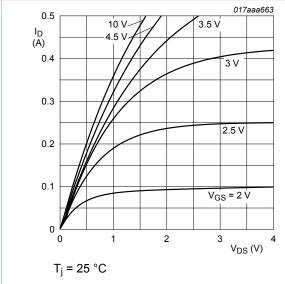


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

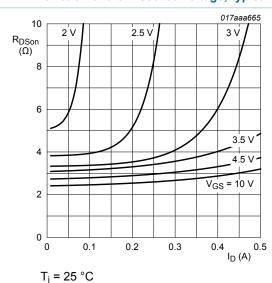


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

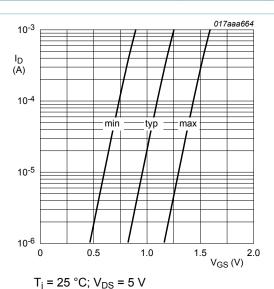


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

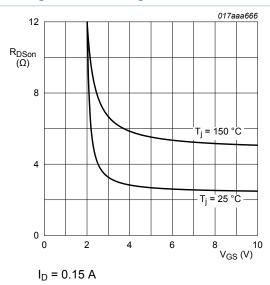


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

60 V, single N-channel Trench MOSFET

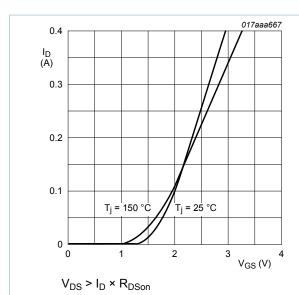


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

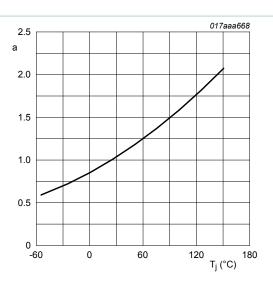


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

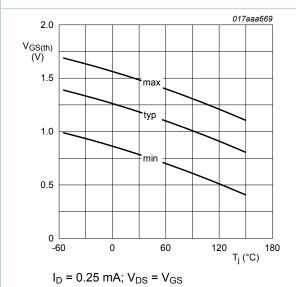
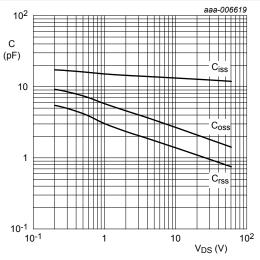


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

60 V, single N-channel Trench MOSFET

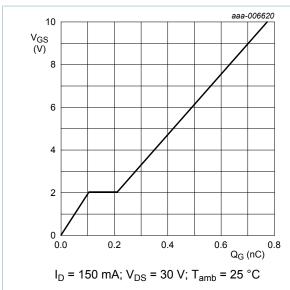


Fig. 15. Gate charge waveform definitions

Q_{GS1}

Q_{GS2}

→ Q_{GD}-Q_{G(tot)}-

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V_{DS} -

 $V_{GS(pl)}$

V_{GS(th)}



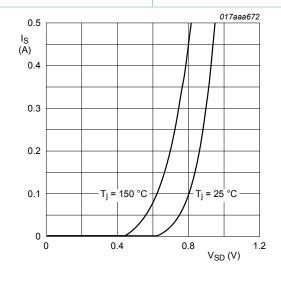
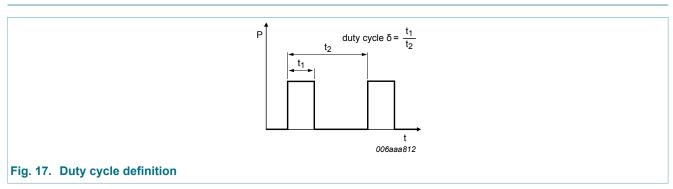


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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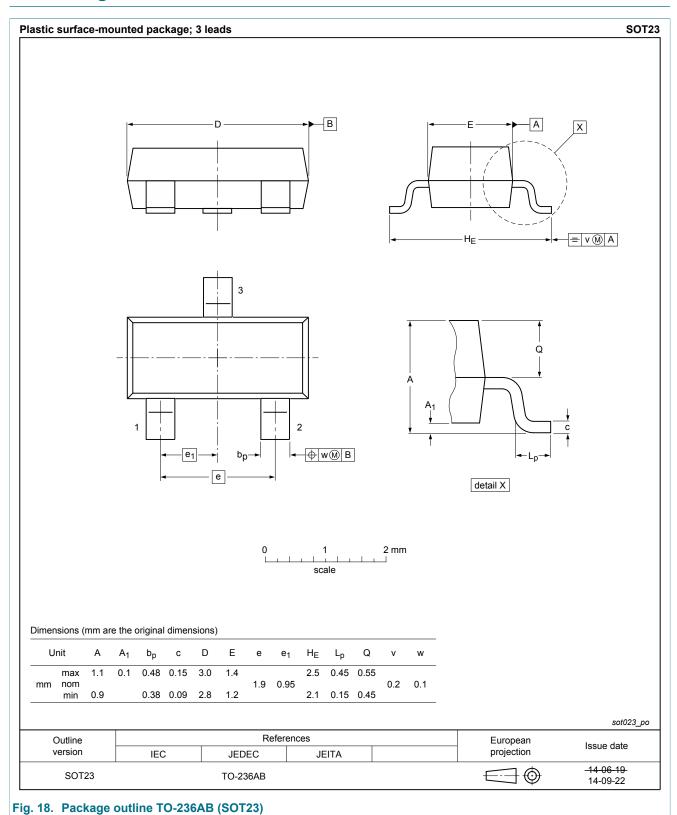
60 V, single N-channel Trench MOSFET

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

60 V, single N-channel Trench MOSFET

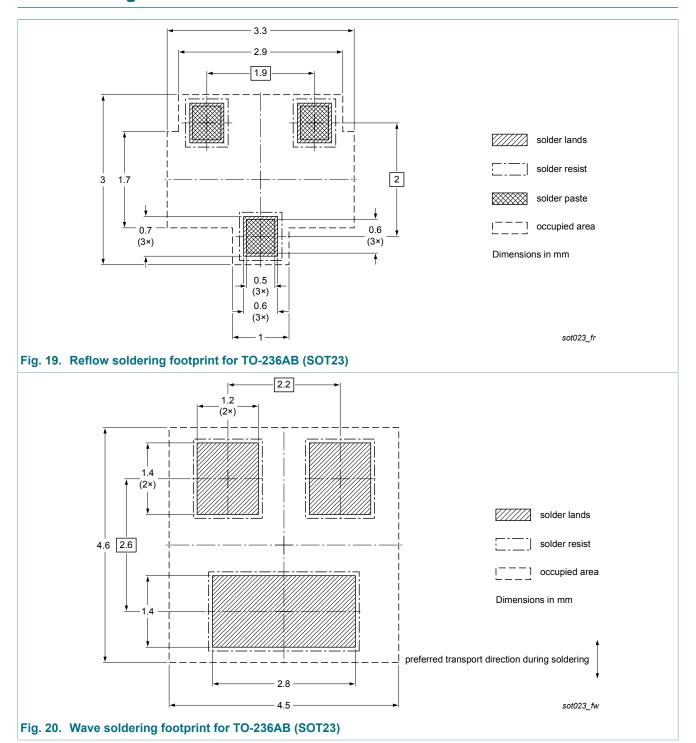
12. Package outline



BSS138AKA

60 V, single N-channel Trench MOSFET

13. Soldering



60 V, single N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BSS138AKA v.3	20150429	Product data sheet	-	BSS138AKA v.2			
Modifications:	Figure 14: x-axis sc	Figure 14: x-axis scale corrected					
BSS138AKA v.2	20141103	Product data sheet	-	BSS138AKA v.1			
BSS138AKA v.1	20130206	Product data sheet	-	-			

60 V, single N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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60 V, single N-channel Trench MOSFET

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60 V, single N-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	9
11.1	Quality information	10
12	Package outline	11
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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